

8-Bit Serial-Input/Serial or Parallel-Output Shift Register with Latched 3-State Outputs

High-Performance Silicon-Gate CMOS

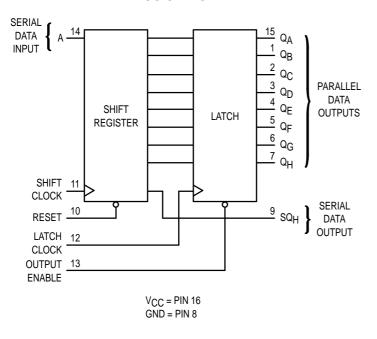
The MC54/74HC595A is identical in pinout to the LS595. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC595A consists of an 8-bit shift register and an 8-bit D-type latch with three-state parallel outputs. The shift register accepts serial data and provides a serial output. The shift register also provides parallel data to the 8-bit latch. The shift register and latch have independent clock inputs. This device also has an asynchronous reset for the shift register.

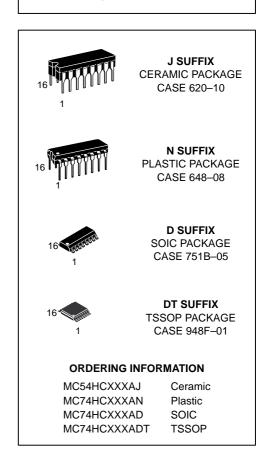
The HC595A directly interfaces with the Motorola SPI serial data port on CMOS MPUs and MCUs.

- Output Drive Capability: 15 LSTTL Loads
- · Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 328 FETs or 82 Equivalent Gates
- Improvements over HC595
 - Improved Propagation Delays
 - 50% Lower Quiescent Power
 - Improved Input Noise and Latchup Immunity

LOGIC DIAGRAM



MC54/74HC595A



PIN ASSIGNMENT										
Q _B [1 ●	16	vcc							
QC [2	15	D QA							
Q _D [3	14	ÞΑ							
Q _E [4	13	OUTPUT ENABLE							
Q _F [5	12	LATCH CLOCK							
Q _G [6	11	SHIFT CLOCK							
QH [7	10	RESET							
GND [8	9] sQ _H							
			•							



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MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 1.5 to V _{CC} + 1.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 35	mA
ICC	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
VCC	DC Supply Voltage (Referenced to GND)		2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	V	
T _A	Operating Temperature, All Package Types	3	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	V _{CC} = 2.0 V V _{CC} = 4.5 V V _{CC} = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
VIH	Minimum High-Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V
VOH	Minimum High-Level Output Voltage, Q _A - Q _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} I_{\text{out}} \le 6.0 \text{ mA} $ $ I_{\text{out}} \le 7.8 \text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
V _{OL}	Maximum Low–Level Output Voltage, Q _A – Q _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{Out} \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL} I_{out} \le 6.0 \text{ mA}$ $ I_{out} \le 7.8 \text{ mA}$	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

^{*} Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C Ceramic DIP: – 10 mW/°C from 100° to 125°C



DC ELECTRICAL CHARACTERISTICS (Continued)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _C C V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
VOH	Minimum High-Level Output Voltage, SQ _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $II_{out}I \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} II_{\text{out}}I \leq 4.0 \text{ mA} \\ II_{\text{out}}I \leq 5.2 \text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	
V _{OL}	Maximum Low–Level Output Voltage, SQ _H	$V_{in} = V_{IH} \text{ or } V_{IL}$ $II_{out}I \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	٧
		$V_{in} = V_{IH} \text{ or } V_{IL} II_{Out}I \leq 4.0 \text{ mA} $ $II_{Out}I \leq 5.2 \text{ mA}$	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
loz	Maximum Three–State Leakage Current, Q _A – Q _H	Output in High-Impedance State $V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	6.0	± 0.5	± 5.0	± 10	μА
lcc	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4.0	40	160	μА

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6.0 \text{ ns}$)

			Gu	aranteed Li	mit	
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 7)	2.0 4.5 6.0	6.0 30 35	4.8 24 28	4.0 20 24	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Shift Clock to SQ _H (Figures 1 and 7)	2.0 4.5 6.0	140 28 24	175 35 30	210 42 36	ns
tPHL	Maximum Propagation Delay, Reset to SQ _H (Figures 2 and 7)	2.0 4.5 6.0	145 29 25	180 36 31	220 44 38	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Latch Clock to Q _A – Q _H (Figures 3 and 7)		140 28 24	175 35 30	210 42 36	ns
tPLZ, tPHZ	Maximum Propagation Delay, Output Enable to Q _A – Q _H (Figures 4 and 8)	2.0 4.5 6.0	150 30 26	190 38 33	225 45 38	ns
tPZL, tPZH	Maximum Propagation Delay, Output Enable to Q _A – Q _H (Figures 4 and 8)	2.0 4.5 6.0	135 27 23	170 34 29	205 41 35	ns
tTLH, tTHL			60 12 10	75 15 13	90 18 15	ns
tTLH, tTHL	Maximum Output Transition Time, SQ _H (Figures 1 and 7)		75 15 13	95 19 16	110 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High–Impedance State), Q _A – Q _H	_	15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Package)*	300	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).



TIMING REQUIREMENTS (Input $t_f = t_f = 6.0 \text{ ns}$)

			Gu	aranteed Li	mit	ĺ
Symbol	Parameter	v _{CC}	25°C to - 55°C	≤ 85°C	≤ 125°C	Unit
t _{Su}	Minimum Setup Time, Serial Data Input A to Shift Clock (Figure 5)	2.0 4.5 6.0	50 10 9.0	65 13 11	75 15 13	ns
t _{Su}	Minimum Setup Time, Shift Clock to Latch Clock (Figure 6)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
th	Minimum Hold Time, Shift Clock to Serial Data Input A (Figure 5)	2.0 4.5 6.0	5.0 5.0 5.0	5.0 5.0 5.0	5.0 5.0 5.0	ns
t _{rec}	Minimum Recovery Time, Reset Inactive to Shift Clock (Figure 2)	2.0 4.5 6.0	50 10 9.0	65 13 11	75 15 13	ns
t _W	Minimum Pulse Width, Reset (Figure 2)	2.0 4.5 6.0	60 12 10	75 15 13	90 18 15	ns
t _W	Minimum Pulse Width, Shift Clock (Figure 1)	2.0 4.5 6.0	50 10 9.0	65 13 11	75 15 13	ns
t _W	Minimum Pulse Width, Latch Clock (Figure 6)	2.0 4.5 6.0	50 10 9.0	65 13 11	75 15 13	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0 4.5 6.0	1000 500 400	1000 500 400	1000 500 400	ns

FUNCTION TABLE

			Inputs				Resulting F	unction	
Operation	Reset	Serial Input A	Shift Clock	Latch Clock	Output Enable	Shift Register Contents	Latch Register Contents	Serial Output SQ _H	Parallel Outputs Q _A – Q _H
Reset shift register	L	Х	Х	L, H, ∕_	L	L	U	L	U
Shift data into shift register	Н	D	5	L, H, ∕_	L	$\begin{array}{c} D \to SR_A; \\ SR_N \to SR_{N+1} \end{array}$	U	$SR_G \to SR_H$	U
Shift register remains unchanged	Н	Х	L, H, ℃	L, H, →	L	U	U	U	U
Transfer shift register contents to latch register	Н	Х	L, H, ~		L	U	$SR_N \to LR_N$	U	SR _N
Latch register remains unchanged	Х	Х	Х	L, H, \	L	*	U	*	U
Enable parallel outputs	Х	Х	Х	Х	L	*	**	*	Enabled
Force outputs into high impedance state	Х	Х	Х	Х	Н	*	**	*	Z

SR = shift register contents LR = latch register contents

D = data (L, H) logic level U = remains unchanged X = don't care Z = high impedance * = depends on Reset and Shift Clock inputs

** = depends on Latch Clock input



PIN DESCRIPTIONS

INPUTS

A (Pin 14)

Serial Data Input. The data on this pin is shifted into the 8-bit serial shift register.

CONTROL INPUTS

Shift Clock (Pin 11)

Shift Register Clock Input. A low—to—high transition on this input causes the data at the Serial Input pin to be shifted into the 8—bit shift register.

Reset (Pin 10)

Active—low, Asynchronous, Shift Register Reset Input. A low on this pin resets the shift register portion of this device only. The 8—bit latch is not affected.

Latch Clock (Pin 12)

Storage Latch Clock Input. A low-to-high transition on this input latches the shift register data.

Output Enable (Pin 13)

Active–low Output Enable. A low on this input allows the data from the latches to be presented at the outputs. A high on this input forces the outputs (Q_A-Q_H) into the high–impedance state. The serial output is not affected by this control unit.

OUTPUTS

Q_A - Q_H (Pins 15, 1, 2, 3, 4, 5, 6, 7)

Noninverted, 3-state, latch outputs.

SQ_H (Pin 9)

Noninverted, Serial Data Output. This is the output of the eighth stage of the 8-bit shift register. This output does not have three-state capability.

MOTOROLA

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SWITCHING WAVEFORMS

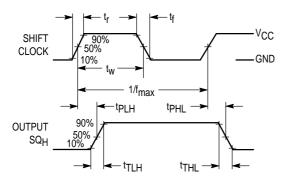


Figure 1.

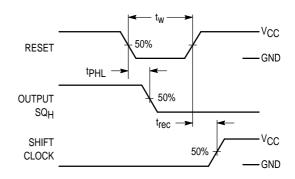


Figure 2.

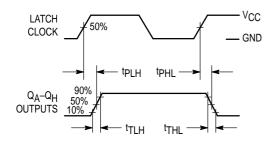


Figure 3.

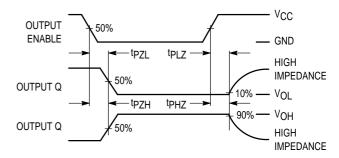


Figure 4.

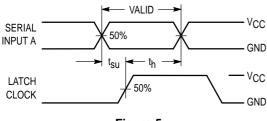


Figure 5.

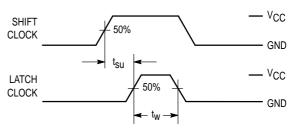
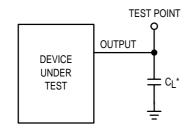


Figure 6.

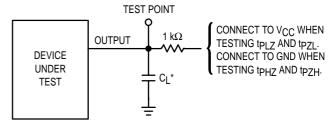
TEST CIRCUITS

6



^{*} Includes all probe and jig capacitance

Figure 7.

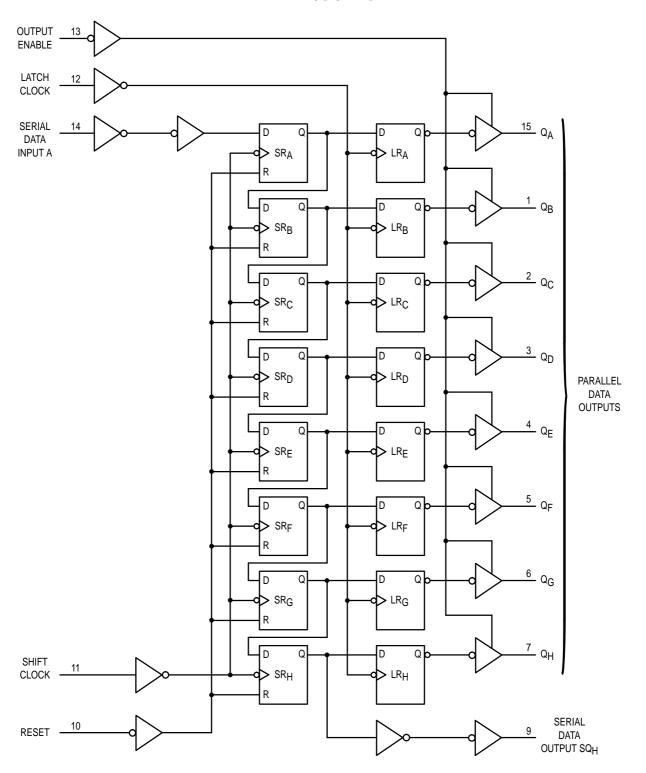


* Includes all probe and jig capacitance

Figure 8.



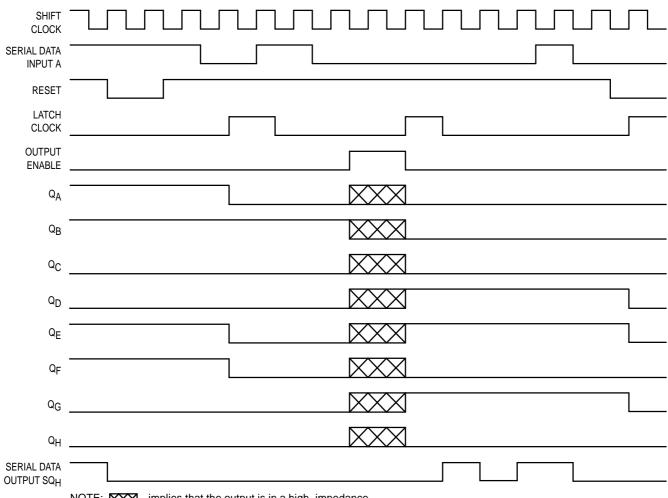
EXPANDED LOGIC DIAGRAM



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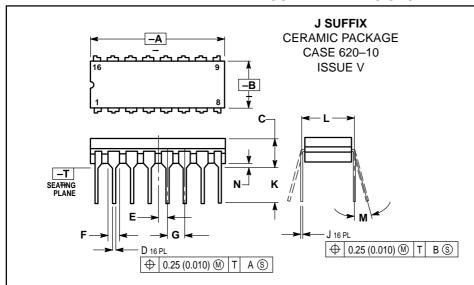
TIMING DIAGRAM



NOTE: implies that the output is in a high-impedance state.



OUTLINE DIMENSIONS



В

C

⊕ 0.25 (0.010) M T A M

F

D 16 PL

-A

G

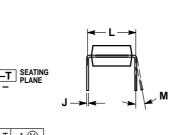
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEAD WHEN
- FORMED PARALLEL.
 DIM F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.750	0.785	19.05	19.93
В	0.240	0.295	6.10	7.49
С	_	0.200	_	5.08
D	0.015	0.020	0.39	0.50
E	0.050	BSC	1.27	BSC
F	0.055	0.065	1.40	1.65
G	0.100	BSC	2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300	BSC	7.62 BSC	
M	0°	15°	0° 15°	
N	0.020	0.040	0.51 1.01	



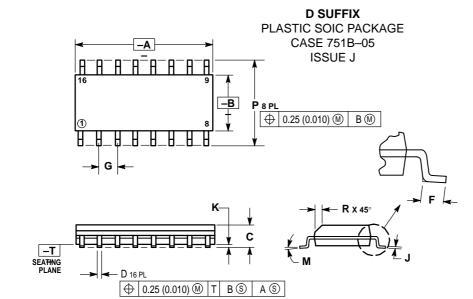
CASE 648-08 ISSUE R



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- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL. DIMENSION B DOES NOT INCLUDE MOLD FLASH. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.	100 BSC	2	.54 BSC
Н	0.	050 BSC	1	.27 BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01



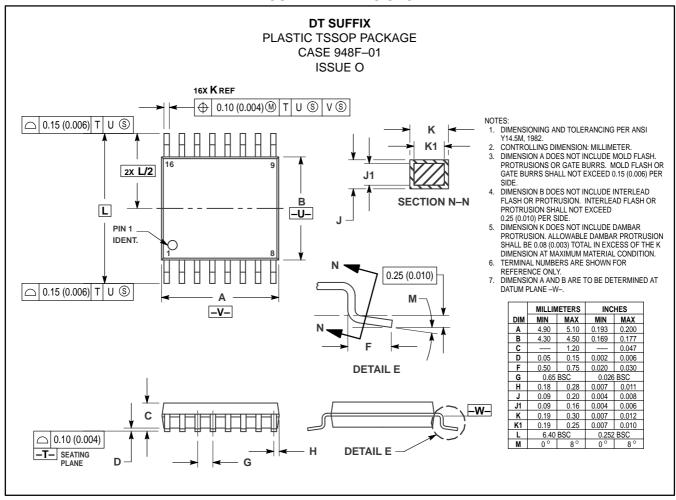
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT

MAXIMUM MATERIAL CONDITION.

	MILLIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019



OUTLINE DIMENSIONS



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